

ZXTP25020DFL 20V, SOT23, PNP low power transistor

Summary

 $BV_{CEO} > -20V$

 $BV_{ECO} > -4V$

 $I_{C(cont)} = 1.5A$

V_{CE(sat)} < 85 mV @ 1A

 $R_{CE(sat)} = 54m\Omega$

 $P_{D} = 350 \text{mW}$

Complementary part number ZXTN25020DFL

Description

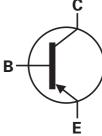
Advanced process capability has been used to achieve high current gain hold up making this device ideal for applications requiring high pulse currents.

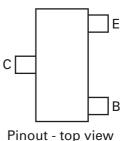


- · High peak current
- · Low saturation voltage

Applications

- · DC-DC converters
- · MOSFET and IGBT gate driving



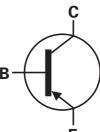


Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020DFLTA	7	8	3000

Device marking

1F2



Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	-25	V
Collector-emitter voltage (forward blocking)	V _{CEO}	-20	V
Emitter-collector voltage (reverse blocking)	V _{ECO}	-4	V
Emitter-base voltage	V _{EBO}	-7	V
Continuous collector current	I _C	-1.5	Α
Base current	I _B	-500	mA
Peak pulse current	I _{CM}	-6	Α
Power dissipation at T _{amb} =25°C ^(a)	P _D	350	mW
Linear derating factor		2.8	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to 150	°C

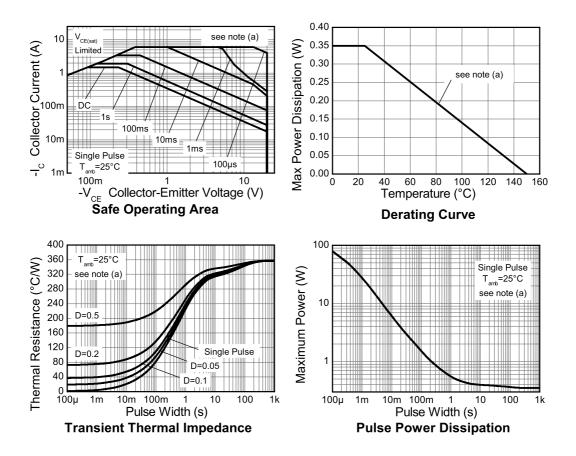
Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	357	°C/W

NOTES:

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Characteristics



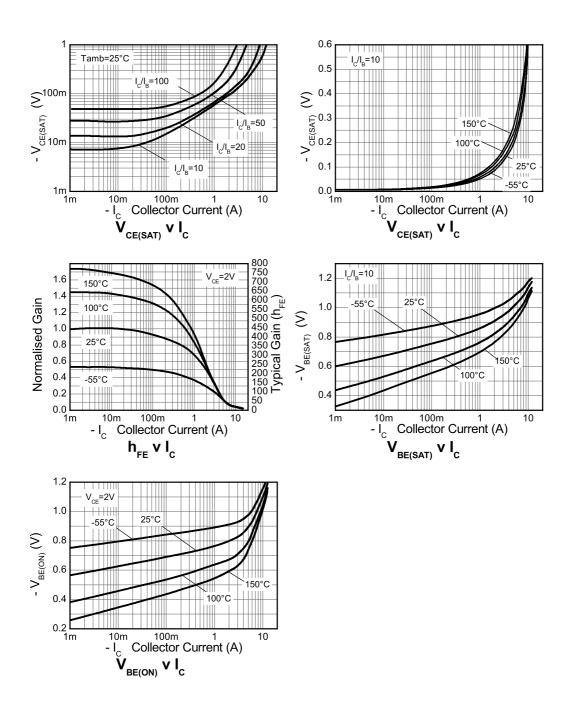
Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	-25	-55		V	I _C = -100μA
Collector-emitter breakdown voltage (base open)	BV _{CEO}	-20	-45		V	I _C = -10mA ^(*)
Emitter-base breakdown voltage	BV _{EBO}	-7	-8.3		V	$I_E = -100 \mu A$
Emitter-collector breakdown voltage (reverse blocking)	BV _{ECO}	-4	-8.5		V	I _E = -100uA ^(*)
Collector cut-off current	I _{CBO}		<-1	-50	nA	V _{CB} = -20V
				-20	μΑ	$V_{CB} = -20V, T_{amb} = 100^{\circ}C$
Emitter cut-off current	I _{EBO}		<-1	-50	nA	V _{EB} = -5.6V
Collector-emitter saturation voltage	V _{CE(sat)}		-65	-85	mV	$I_C = -1A$, $I_B = -100 \text{mA}^{(*)}$
Voitage			-160	-225	mV	$I_C = -1A$, $I_B = -10mA^{(*)}$
			150	-195	mV	$I_C = -1.5A$, $I_B = -30mA^{(*)}$
			-210	-275	mV	$I_C = -2A$, $I_B = -40 \text{mA}^{(*)}$
			-215	260	mV	$I_C = -4A$, $I_B = -400 \text{mA}^{(*)}$
Base-emitter saturation voltage	V _{BE(sat)}		-845	-950	mV	$I_C = -1.5A$, $I_B = -30mA^{(*)}$
Base-emitter turn-on voltage	V _{BE(on)}		-785	-900	mV	I _C = -1.5A, V _{CE} = -2V ^(*)
Static forward current transfer	h _{FE}	300	450	900		$I_C = -10 \text{mA}, V_{CE} = -2V^{(*)}$
ratio		160	250			$I_C = -1.5A, V_{CE} = -2V^{(*)}$
		60	90			$I_C = -4A$, $V_{CE} = -2V^{(*)}$
			15			$I_C = -10A$, $V_{CE} = -2V^{(*)}$
Transition frequency	f _T		290		MHz	I _C = -50mA, V _{CE} = -10V f = 50MHz
Output capacitance	C _{obo}		21	30	pF	V _{CB} = -10V, f = 1MHz ^(*)
Delay time	t _(d)		14.2			$V_{CC} = -10V. I_C = -1A, I_{B1}$
Rise time	t _(r)		16.3			= I _{B2} = -50mA.
Storage time	t _(s)		186			
Fall time	t _(f)		32.7			

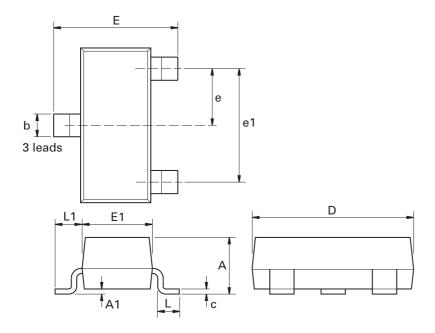
NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

Typical characteristics



Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
Α	-	1.12	=	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.120	0.003	0.008	L	0.25	0.62	0.018	0.024
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.0375	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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